

b) Amendments to the Claims

Please amend claim 1 as follows. A detailed listing of all the claims that are or were in the application is provided.

--1. (Currently Amended) A sputtering method for forming a film on a substrate in a film forming space while monitoring emission intensity of plasma, the method comprising the steps of:

detecting a thickness of the film formed on said substrate;
comparing a detected value with a preset value of the film thickness;
deciding a target value of the emission intensity that will provide the preset value of the film thickness in accordance with a compared result; and
adjusting the emission intensity to the target value[[.]] to increase a transmittance of the film formed on the substrate to compensate for an increase in resistance of the film.

2. (Previously Presented) The sputtering method according to claim 1, further comprising controlling a flow rate of at least one gas introduced into said film forming space, thereby adjusting the intensity to the target value of the emission intensity.

3. (Previously Presented) The sputtering method according to Claim 1, wherein a target containing In is employed as a sputtering target.

4. (Previously Presented) The sputtering method according to Claim 1, wherein a cylindrical rotating target is employed as a sputtering target.

5. (Previously Presented) The sputtering method according to Claim 2, wherein oxygen gas is selected as the gas for which the flow rate is controlled.

6. (Previously Presented) The sputtering method according to Claim 1, wherein the target value of the emission intensity is set to fall in a predetermined range defined beforehand.

7. (Previously Presented) The sputtering method according to Claim 6, wherein if the target value deviates from said predetermined range, sputtering is stopped.

8. (Previously Presented) A sputtering apparatus comprising a film forming container, a substrate feeding mechanism, and an emission intensity monitor, the apparatus further comprising:

a film thickness measuring device, configured to measure a thickness of a film formed on a substrate and outputting a measured result;

a comparator, configured to compare an output of said film thickness measuring device with a preset value of the film thickness and to output a target value of said emission intensity monitor in accordance with a compared result; and

an emission intensity target-value setting unit, configured to receive the output target value from the comparator, and to adjust the emission intensity to the target value.

9. (Previously Presented) The sputtering apparatus according to Claim 8, wherein the emission intensity target-value setting unit comprises a gas flow rate control mechanism for receiving the target value of said emission intensity monitor and controlling a flow rate of at least one of gases introduced to said film forming container in accordance with the target value.--